

NTR4501N

Power MOSFET

20 V, 3.2 A, Single N-Channel, SOT-23

Features

- Leading Planar Technology for Low Gate Charge / Fast Switching
- 2.5 V Rated for Low Voltage Gate Drive
- SOT-23 Surface Mount for Small Footprint
- Pb-Free Package is Available

Applications

- Load/Power Switch for Portables
- Load/Power Switch for Computing
- DC-DC Conversion

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±12	V
Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	3.2	A
		T _A = 85°C		2.4	A
Steady State Power Dissipation (Note 1)	Steady State		P _D	1.25	W
Pulsed Drain Current	t _p = 10 μs		I _{DM}	10.0	A
Operating Junction and Storage Temperature			T _J , T _{STG}	−55 to 150	°C
Continuous Source Current (Body Diode)			I _S	1.6	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction-to-Ambient (Note 2)	$R_{\theta JA}$	300	

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size.

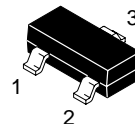
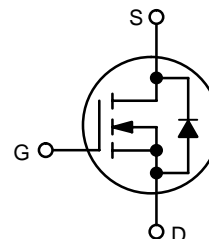


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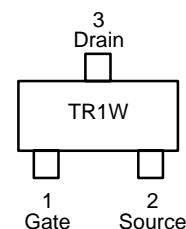
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX (Note 1)
20 V	70 m Ω @ 4.5 V	3.6 A
	85 m Ω @ 2.5 V	3.1 A

N-Channel



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



TR1 = Specific Device Code
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NTR4501NT1	SOT-23	3000 / Tape & Reel
NTR4501NT3	SOT-23	10000 / Tape & Reel
NTR4501NT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NTR4501NT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTR4501N

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3)	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20	24.5		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			22		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$			1.5	μA
		$V_{DS} = 16\text{ V}$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA

ON CHARACTERISTICS

Gate Threshold Voltage (Note 3)	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	0.65		1.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-2.3		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 3.6\text{ A}$		70	80	m Ω
		$V_{GS} = 2.5\text{ V}, I_D = 3.1\text{ A}$		85	105	
Forward Transconductance	g_{FS}	$V_{DS} = 5.0\text{ V}, I_D = 3.6\text{ A}$		9		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 10\text{ V}$		200		pF
Output Capacitance	C_{OSS}			80		
Reverse Transfer Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}, I_D = 3.6\text{ A}$		2.4	6.0	nC
Gate-to-Source Gate Charge	Q_{GS}			0.5		
Gate-to-Drain Charge	Q_{GD}			0.6		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}, I_D = 3.6\text{ A}, R_G = 6.0\text{ }\Omega$		6.5		ns
Rise Time	t_r			12		
Turn-Off Delay Time	$t_{d(OFF)}$			12		
Fall Time	t_f			3		

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_{SD} = 1.6\text{ A}$		0.8	1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 1.6\text{ A}$		7.1		ns
Charge Time	t_a			5		
Discharge Time	t_b			1.9		
Reverse Recovery Charge	Q_{RR}			3.0		nC

3. Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

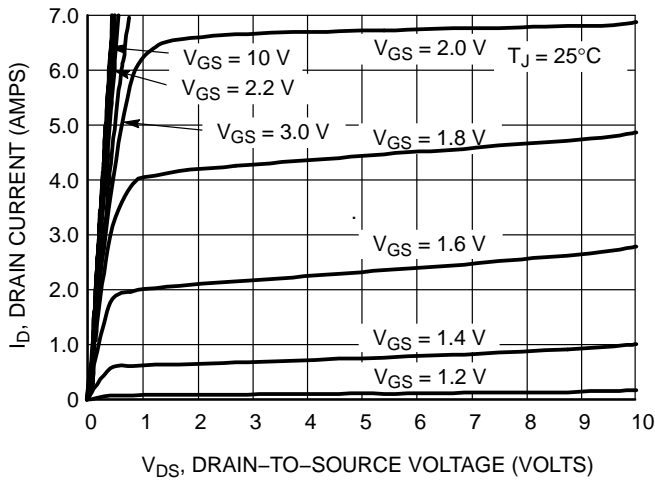


Figure 1. On-Region Characteristics

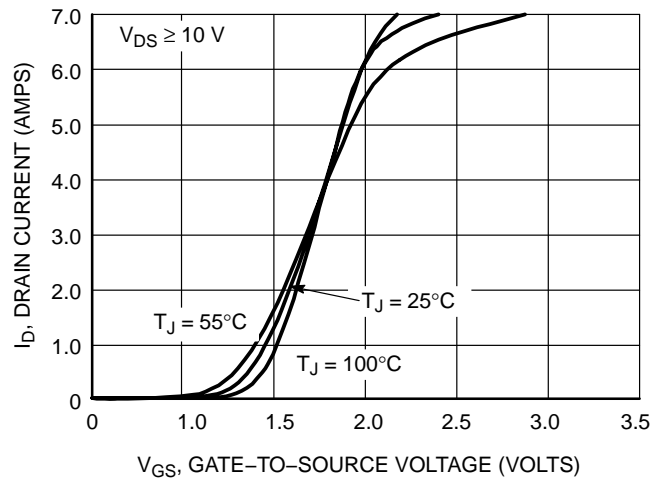


Figure 2. Transfer Characteristics

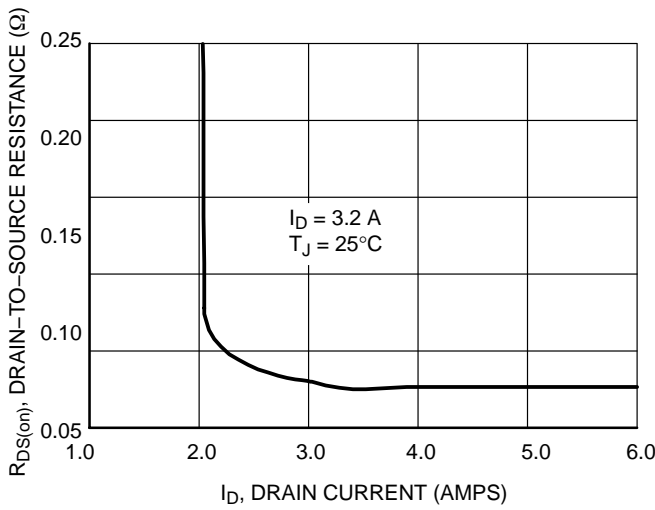


Figure 3. On-Resistance versus Gate-to-Source Voltage

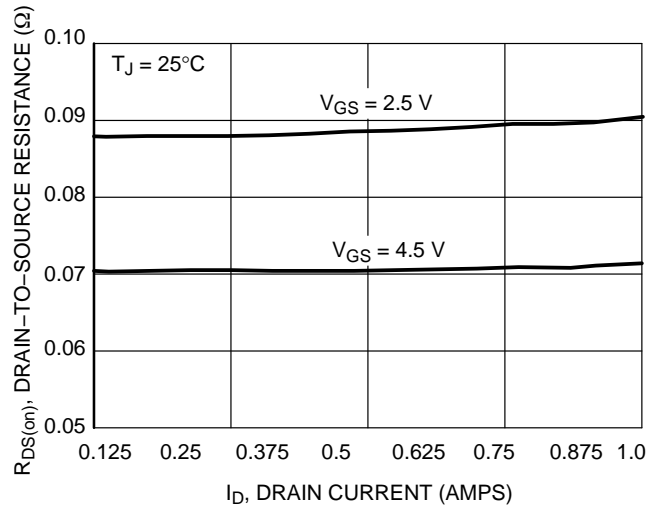


Figure 4. On-Resistance versus Drain Current and Gate Voltage

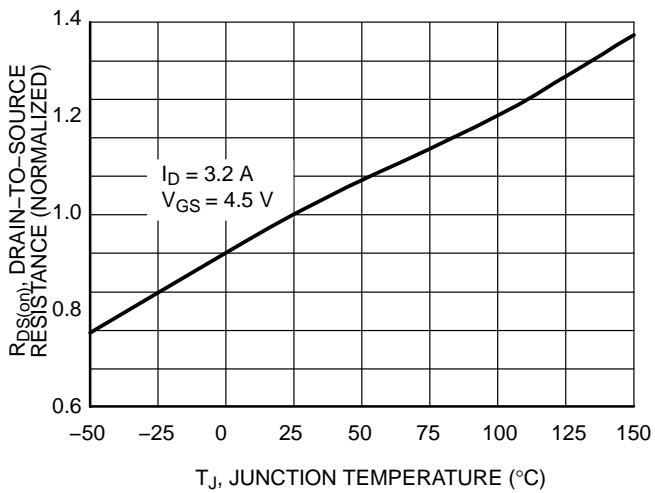


Figure 5. On-Resistance Variation with Temperature

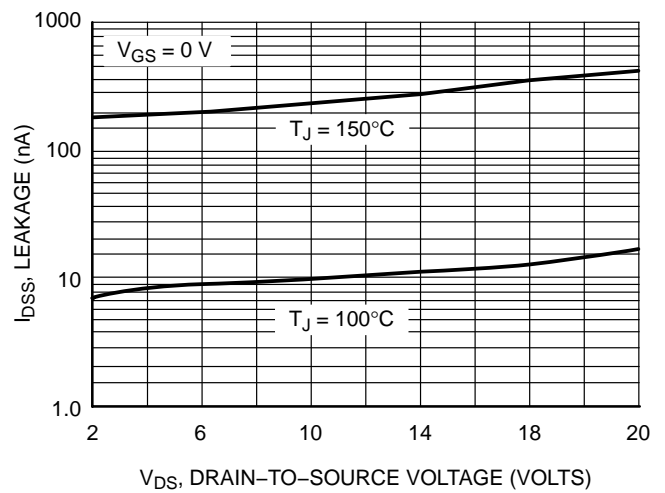


Figure 6. Drain-to-Source Leakage Current versus Voltage

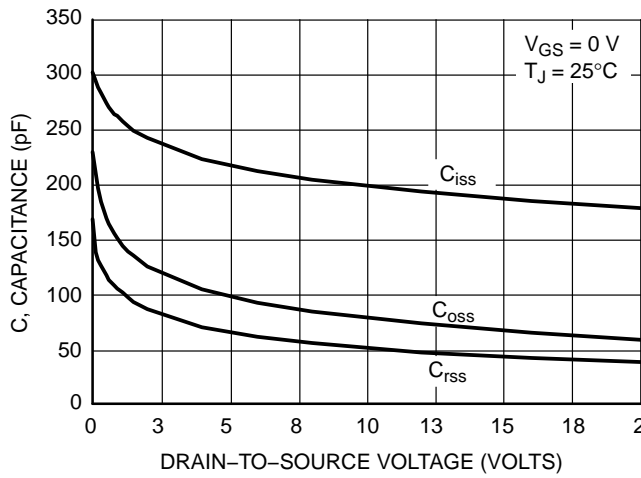


Figure 7. Capacitance Variation

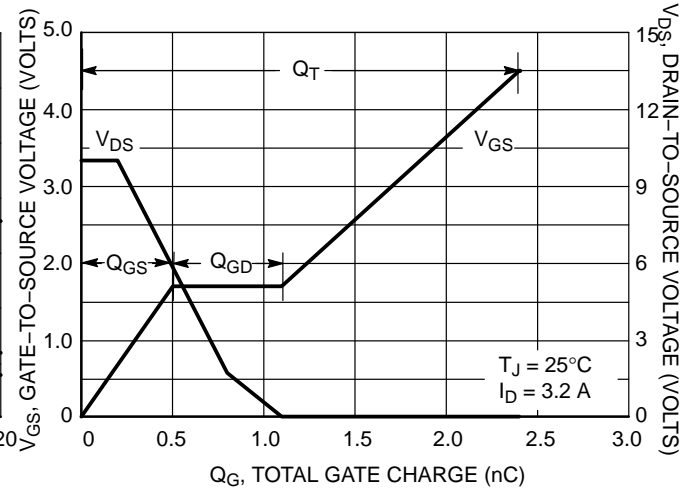


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Gate Charge

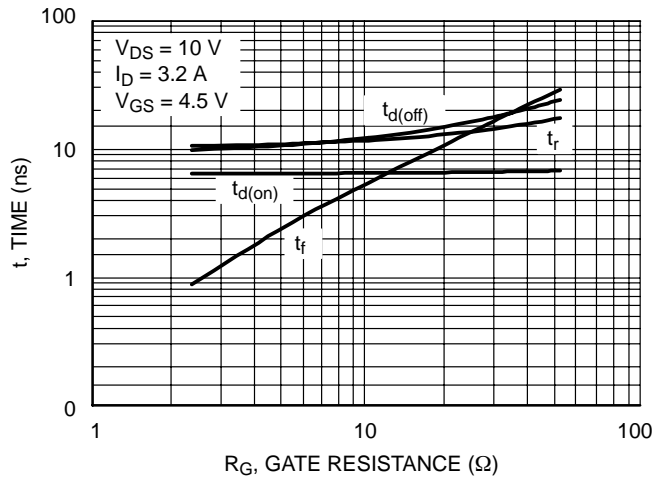


Figure 9. Resistive Switching Time Variation versus Gate Resistance

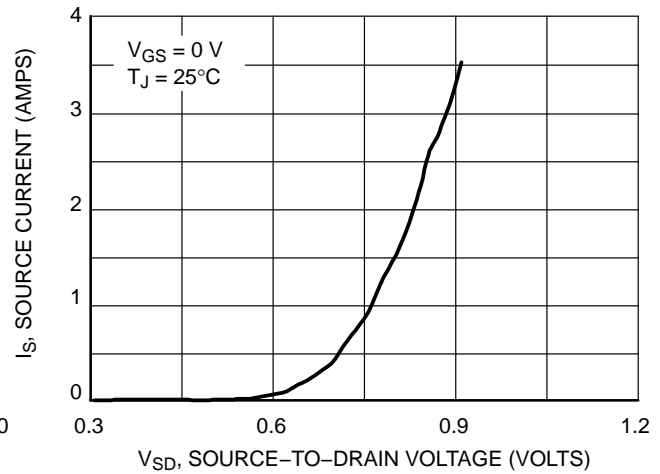
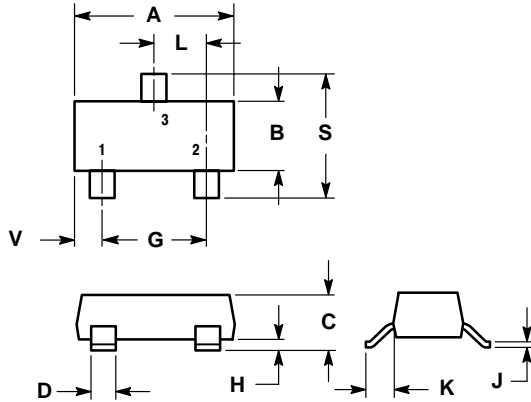


Figure 10. Diode Forward Voltage versus Current

NTR4501N

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-09
ISSUE AH



NOTES:

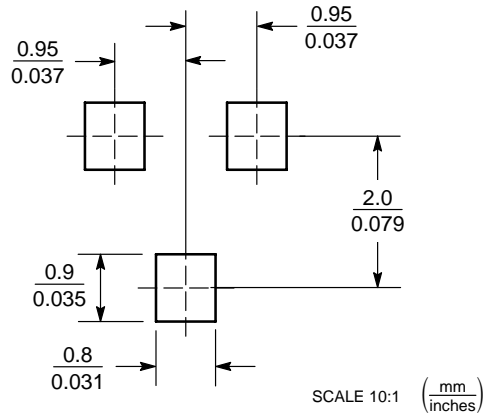
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01, -02, AND -06 OBSOLETE, NEW STANDARD 318-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60


STYLE 21:

- PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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